

## ESE532: System-on-a-Chip Architecture

Day 23: November 19, 2018  
Estimating Chip Area and Costs



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## Today

- Chip Costs from Area
- Chip Area
  - IO
  - Interconnect – Rent's Rule
  - Infrastructure
- Some Areas
  - CACTI – for modeling memories

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## Message

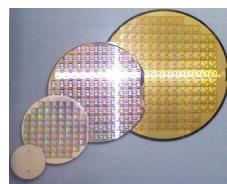
- First order:
  - Chip cost proportional to Area
  - Area = Sum(Area(Components))
- But appreciate the simplification:
  - Yield makes cost superlinear in area
  - I/O, Interconnect, infrastructure
    - Can make Area > Sum(Area(Components))

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## Wafer Cost

- Incremental cost of producing a silicon wafer is fixed for a given technology
  - Independent of the specific design
  - E.g. \$3,500
- Can fill wafer with copies of chip



By German Wikipediabatch, original upload 7.  
Okt 2004 by Stahlkocher de:Bild:Wafer 2 Zoll bis 8 Zoll.jpg,  
CC BY-SA 3.0, <https://commons.wikimedia.org/w/index.php?curid=928106>

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## Preclass 1

- Rough cost per mm of silicon?
  - \$3500 for 300mm wafer

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## Implication

- Raw silicon die cost is roughly proportional to area
  - Larger the die, the fewer we get on the wafer

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## ...but

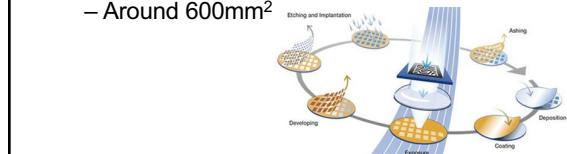
- Limits to how big we can make chips
  - Manufacturers are prepared to create
  - Can be reliably manufactured
- ...and how small we can make chips
  - I/O pads
  - Cutting/handling/marketing

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## Imaging

- Limit to how large optical imaging supports
- Reticle – imagable region for photo lithography
  - Around  $600\text{mm}^2$



Source: <https://www.sem.com/the-exposure-apparatus-is-the-most-expensive-and-complex-step-in-the-chip-fabrication-process-what-is-involved-in-the-lithography-business>; jd:428145?nd=147109

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## Yield

- Chips won't be manufactured perfectly
  - Dust particles can impact imaging
  - Manufacturing processes are statistical
- If chips must be defect-free,
  - larger chips are more likely to have defects than smaller chips

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## Simple Yield Model

- Probability of a region being perfect
  - E.g. probability of one sq. mm being defect-free
- Chip yields if its entire area is defect free

(look at how to tolerate defects in a couple of weeks)

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## Chip Yield

- $P$  = defect-free probability per sq. mm
- What is probability a chip of  $A$  sq. mm yields (symbolic)?

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## Preclass 2

- $P=0.99$
- Probability of yield for
  - $10\text{ mm}^2$ ,  $50\text{ mm}^2$ ,  $100\text{ mm}^2$ ,  $500\text{ mm}^2$

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## Yielded Die

- For a yield rate, Y, how many raw die need to manufacture per yielded die?

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## Preclass 3

- P=0.99
- Die cost for:
  - 10 mm<sup>2</sup>, 50 mm<sup>2</sup>, 100 mm<sup>2</sup>, 500 mm<sup>2</sup>

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## Yielded Die Cost

$$Cost = \frac{Raw}{Yield} = \frac{A^* Cost/mm^2}{P^A}$$

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## Yielded Die Cost

$$Cost = \frac{Raw}{Yield} = \frac{A^* Cost/mm^2}{P^A}$$

- Ultimately exponential in Area
- Means
  - Expensive above knee in exponential curve
  - Close to linear below knee in curve
- E.g.
  - Below P<sup>A</sup>=0.5
  - effect of Yield term is less than 2

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## Design Dependent Cost

- P can be design dependent
  - More aggressive designs have higher defect rates
  - Can tune design to ease manufacturing
- Contrast with point that wafer manufacture cost independent of design

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## Slightly Fuller Story

- Chip cost = die + test + package

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## Test

- Testing costs proportional to test time
  - Time on expensive test unit
  - Depends on complexity of tests need to run
    - Can motivate spending silicon area on on-chip test structures to reduce
- Can dominate on small chips or complex testing

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## Packaging

- Pay for density and performance

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## Plastic Packages

- Simple plastic packages cheap
  - Limited number of pins
    - Limited to perimeter
  - Limited heat removal (few Watts)
  - Can be large (due to pins)
  - Higher inductance on pins



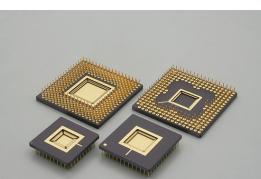
[http://wiki.electroons.com/doku.php?id=ic\\_packages](http://wiki.electroons.com/doku.php?id=ic_packages)

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## Ceramic Packages

- Better thermal characteristics
  - Add heat-sink, tolerate hotter chips
    - To 100 W
  - More pins
  - More expensive

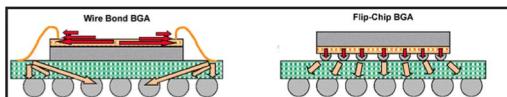


Source: [https://www.ngkntk.co.jp/english/product/semiconductor\\_packages/htcc.html](https://www.ngkntk.co.jp/english/product/semiconductor_packages/htcc.html)

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## Flip Chip Packages

- Support Area-IO
  - More, denser pins
  - Smaller die if IO limited
  - Lower inductances
  - Smaller packaged chip

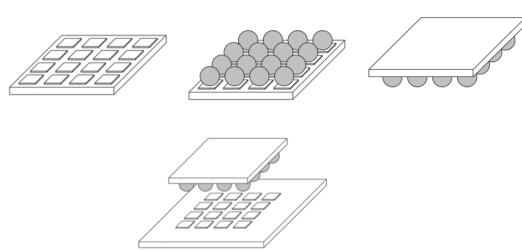


Source: <http://mantravlsi.blogspot.com/2014/10/flip-chip-and-wire-bonding.html>

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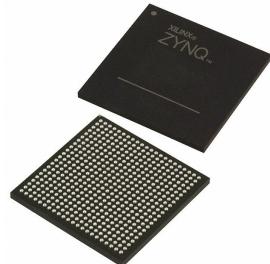
## Flip Chip I/O



Source: [https://en.wikipedia.org/wiki/Flip\\_chip](https://en.wikipedia.org/wiki/Flip_chip)

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## Zynq Land Grid Package



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## Don't Forget NRE

- This is all about recurring costs
- Cost = RecurringCost + (NRE/NumParts)
- NRE
  - Mask costs in millions
  - Design costs in 10s to 100s of millions

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## Putting Together

- 100mm<sup>2</sup> die -- \$5 raw
  - Maybe \$6--13 yielded -- call it \$6
- NRE \$100 M -- \$1
  - Sell 100 M units
- Put in \$1 package -- \$1
- Test -- \$1
- Total: \$9

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## Price vs. Cost

- ...and this is all about **cost**
  - What it takes to manufacture
- Price
  - What people will pay for it
- Profit = Price - Cost

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## Area

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## Area

- Simple story
  - Sum up component areas

$$A = \sum_i A_i$$

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## Too Simplistic

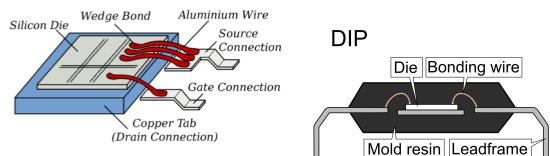
- Area may be driven by
  - I/O
  - Interconnect
- Will need to pay for infrastructure
  - Clocking, Power

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## I/O Pads

- Must go on edge for wire bonding
  - Esp. for cheap packages



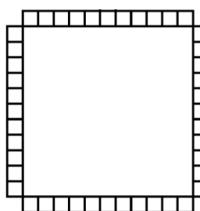
Src: <http://en.wikipedia.org/wiki/File:Wirebonding2.svg>

Source: [https://commons.wikimedia.org/wiki/File:DIP\\_package\\_sideview.PNG](https://commons.wikimedia.org/wiki/File:DIP_package_sideview.PNG)

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## Pad Ring

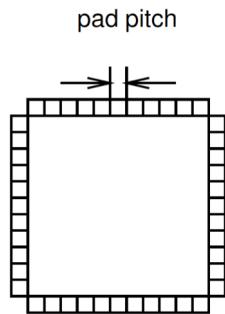
- Pads must go on side of chip
- Pad spacing large to permit bonding
- I/O pads may set lower bound on chip size



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## Preclass 4

- 400 pads
- 25µm pad spacing
- **Square chip dimensions?**



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## I/O Limits

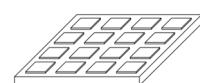
- Perimeter grows as 4s
- Area grows as s<sup>2</sup>
- Area grows (NumIO/4)<sup>2</sup>
- IO may drive chip area

$$A = \text{Max} \left( \left( \sum_i A_i \right), \left( \frac{\text{NumIO}}{4 \times \text{PadPitch}} \right)^2 \right)$$

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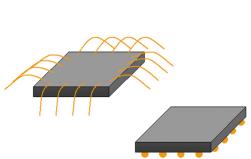
## Area I/O

- Put I/O in grid over chip
- I/O pads still large and take up space
- Avoid perimeter scaling
- Requires more expensive flip-chip package

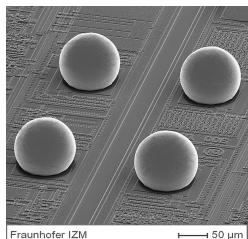


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## Flip Chip, Area IO



[www.microwavejournal.com](http://www.microwavejournal.com)



Fraunhofer IZM 50 μm

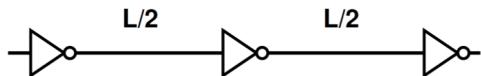
[http://www.izm.fraunhofer.de/en/abteilungen/high\\_density\\_interconnectwaferlevelpackaging/arbeitsgebiete/arbeitsgebiet1.html](http://www.izm.fraunhofer.de/en/abteilungen/high_density_interconnectwaferlevelpackaging/arbeitsgebiete/arbeitsgebiet1.html)

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## Interconnect

- Long wires need buffering
- Buffers take up space
  - Weren't in simple accounting of logic and memory blocks



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## Interconnect

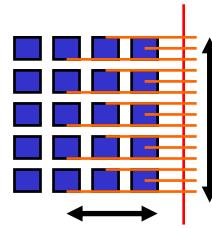
- Wires take up space
- Similar issue to pad I/O
  - Wires crossing into region grow as perimeter
  - Logic inside grows as area
- Region size may be dictated by wires entering/leaving

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## Wiring Requirements

- Wires 50nm pitch
- Gates 500nm on side
  - (500nm x 500nm)
- How many gates per row can provide outputs before saturate edge?
  - (single layer)
- What if want more outputs to exit across edge?

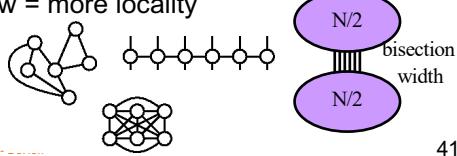


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## Bisection Width

- Partition design into two equal size halves
  - Minimize wires (nets) with ends in both halves
- Number of wires crossing is **bisection width**
  - Information crossing
- lower bw = more locality



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## Rent's Rule

- If we recursively bisect a graph, attempting to minimize the cut size, we typically get:

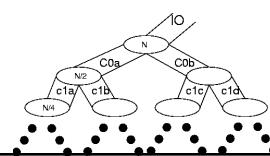
$$BW = IO = c N^p$$

$$-0 \leq p \leq 1$$

- $p \leq 1$  means many inputs come from within a partition

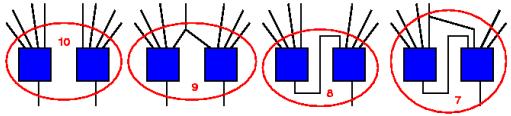
[Landman and Russo,  
IEEE TR Computers p1469, 1971]

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## Rent and Locality

- Rent and IO quantifying locality
    - local consumption
    - local fanout
- $$IO = c N^p$$

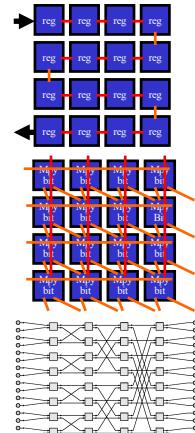


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## Common Applications

- Rent  $p=0$ 
  - Shift-register, 1D filter
- Rent  $p=0.5$ 
  - Array multiplier
  - 2D Window Filter
  - nearest-neighbor
- Rent  $p=1.0$ 
  - FFT, Sort

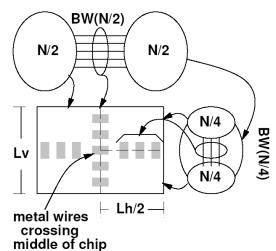


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## VLSI Interconnect Area

- Bisection width is lower-bound on IC width
  - When wire dominated, may be tight bound
- (recursively)
- Rent's Rule tells us how big our chip must be



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## As a function of Bisection

- $A_{\text{chip}} \geq N \times A_{\text{gate}}$
- $A_{\text{chip}} \geq N_{\text{horizontal}} W_{\text{wire}} \times N_{\text{vertical}} W_{\text{wire}}$
- $N_{\text{horizontal}} = N_{\text{vertical}} = IO = c N^p$
- $A_{\text{chip}} \geq (cN)^{2p}$
- If  $p < 0.5$   
 $A_{\text{chip}} \propto N$
- If  $p > 0.5$   
 $A_{\text{chip}} \propto N^{2p}$

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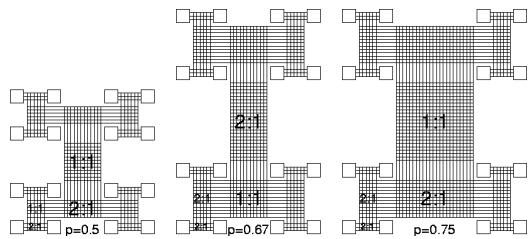
## In terms of Rent's Rule

- If  $p < 0.5$ ,  $A_{\text{chip}} \propto N$
- If  $p > 0.5$ ,  $A_{\text{chip}} \propto N^{2p}$
- Typical designs have  $p > 0.5$ 
  - interconnect dominates
  - $A_{\text{chip}} > \sum A_{\text{elements}}$

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## Rent Network Richness



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## Infrastructure: Clocking

- PLL (Phased-Lock-Loop) to generate and synchronize clock
- Clock drivers are big (drive big load)
- Need buffering all over chip

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## Infrastructure: Power

- Need many I/O Pads
  - Carry current
  - Keep inductance low
- Wires to distribute over chip
- Maybe
  - Capacitance to stabilize power
  - Voltage converters

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$$\text{Area} \quad A = \sum_i A_i$$

- Mostly sum of components, but...
- Area may be driven by
  - I/O
  - Interconnect  $A \geq N^{2p}$
- Will need to pay for infrastructure
  - Clocking, Power

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## Some Areas

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## Processor Areas

- ARM Cortex A9 about  $1\text{mm}^2$  in 28nm
  - Zynq processor
  - SuperScalar core
- A5 (scalar) about  $0.25\text{mm}^2$
- A15 (higher performance) about  $3\text{mm}^2$

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## Zynq Compute Blocks

- Crude estimate, including interconnect
- 2000 6-LUTs per sq. mm
  - DSP Block  $\sim 0.1$  sq. mm

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## CACTI

- Standard program for modeling memories and caches
  - More sophisticated version of the simple modeling we've been doing
- Will ask you to use for custom area estimates (P4 milestone, final report)

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## CACTI Parameters

- Technology
- Capacity
- Output Width
- Ports
- Cache ways

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## Example Output

- Total cache size (bytes): 32768  
Number of banks: 1  
Associativity: 4  
Block size (bytes): 64  
Read/write Ports: 1  
Read ports: 0  
Write ports: 0  
Technology size (nm): 32  
  
Access time (ns): 1.09421  
Cycle time (ns): 1.25458  
Total dynamic read energy per access (nJ): 0.0234295  
Total dynamic write energy per access (nJ): 0.018806  
Total leakage power of a bank without power gating, including its netw  
Cache height x width (mm): 0.152304 x 0.523289

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## CACTI – Memories on Zynq

- 32nm (closest technology it models to 28nm in Zynq)
- 36Kb BRAMs 0.025mm
  - 2 port, 72b output
- ARM L1 cache 0.08mm
  - 32KB 4-way associative (previous slide)
- ARM L2 cache 1.5 mm
  - 512KB 8-way associative

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## Zynq Component Estimates

- 6-LUT 0.0005 mm<sup>2</sup>
- DSP Block 0.1 mm<sup>2</sup>
- 36Kb BRAMs 0.025mm<sup>2</sup>
- ARM L1 cache 0.08mm<sup>2</sup>
- ARM L2 cache 1.5 mm<sup>2</sup>
- ARM Cortex A9 1.0 mm<sup>2</sup>

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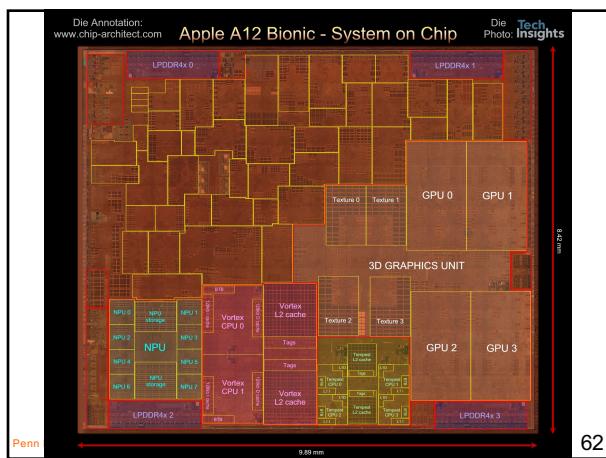
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## Apple A11



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- 90mm<sup>2</sup> 10nm FinFET
- 4.3B transistors
- iPhone 8, 8s, X
- 6 ARM cores
  - 2 fast (2.4GHz)
  - 4 low energy
- 3 custom GPUs
- Neural Engine
  - 600 Bops?
- Motion, image accel.
- Tech Insights 8MB L2 cache

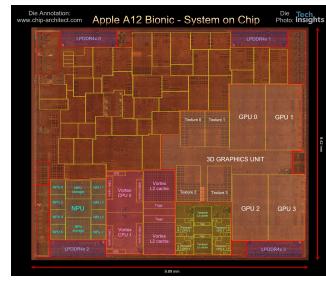


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## Apple A12

- 84mm<sup>2</sup>, 7nm
- 7 Billion Tr.
- iPhone XS
- 6 ARM cores
  - 2 fast
  - 4 low energy
- 4 custom GPUs
- Neural Engine
- – 5 Trillion ops/s?



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## A12 Die Areas

Die Block Comparison (mm<sup>2</sup>)

SoC	Apple A12	Apple A11
Process Node	TSMC N7	TSMC 10FF
Total Die	83.27	87.66
Big Core	2.07	2.68
Small Core	0.43	0.53
CPU Complex (incl. cores)	11.90	14.48
GPU	14.88	15.28
GPU Core	3.23	4.43

<https://www.anandtech.com/print/13393/techinsights-publishes-apple-a12-die-shot-our-take>  
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## Big Ideas

- First order:
  - Chip cost proportional to Area
  - Area = Sum(Area(Components))
- But appreciate the simplification:
  - Yield makes cost superlinear in area
  - Limited range over which “linear” accurate
  - I/O, Interconnect, infrastructure
    - Can make Area > Sum(Area(Components))

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## Admin

- Tomorrow
  - Is a virtual Thursday
    - There are TA office hours
    - I will have “Tuesday” office hours
      - But running to airport right at 5:25pm
- Wednesday is a virtual “Friday”
  - No lecture
- Friday is a Holiday – no milestone due
- P4 due Friday, Nov. 30<sup>th</sup>
- Proj. supplement – additional instructions for turnin and run final proj.

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